

HIGH-SPEED 3.3V 64K x 36 ASYNCHRONOUS DUAL-PORT STATIC RAM

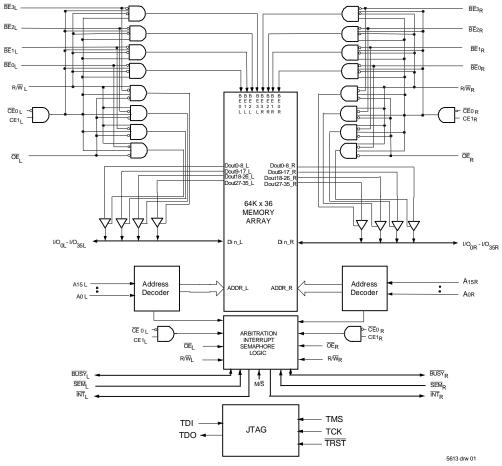
PRELIMINARY IDT70V658S

Features

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed access
 - Commercial: 10/12/15ns (max.)
 - Industrial: 12/15ns (max.)
- Dual chip enables allow for depth expansion without external logic
- IDT70V658 easily expands data bus width to 72 bits or more using the Master/Slave select when cascading more than one device
- M/S = VIH for BUSY output flag on Master,
 M/S = VIL for BUSY input on Slave
- Busy and Interrupt Flags
- On-chip port arbitration logic

- Full on-chip hardware support of semaphore signaling between ports
- Fully asynchronous operation from either port
- Separate byte controls for multiplexed bus and bus matching compatibility
- Supports JTAG features compliant to IEEE 1149.1
- LVTTL-compatible, single 3.3V (±150mV) power supply for core
- LVTTL-compatible, selectable 3.3V (±150mV)/2.5V (±100mV) power supply for I/Os and control signals on each port
- Available in 208-pin Plastic Quad Flatpack, 208-ball fine pitch Ball Grid Array, and 256-ball Ball Grid Array
- Industrial temperature range (-40°C to +85°C) is available for selected speeds

Functional Block Diagram



NOTES:

- 1. BUSY is an input as a Slave (M/S=VIL) and an output when it is a Master (M/S=VIH).
- 2. BUSY and INT are non-tri-state totem-pole outputs (push-pull).

JUNE 2001

Description

The IDT70V658 is a high-speed 64K x 36 Asynchronous Dual-Port Static RAM. The IDT70V658 is designed to be used as a stand-alone 2304K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 72-bit-or-more word system. Using the IDT MASTER/ SLAVE Dual-Port RAM approach in 72-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control,

address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (either $\overline{\text{CE}}_0$ or CE1) permit the on-chip circuitry of each port to enter a very low standby power mode.

The 70V658 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controlled by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3V.

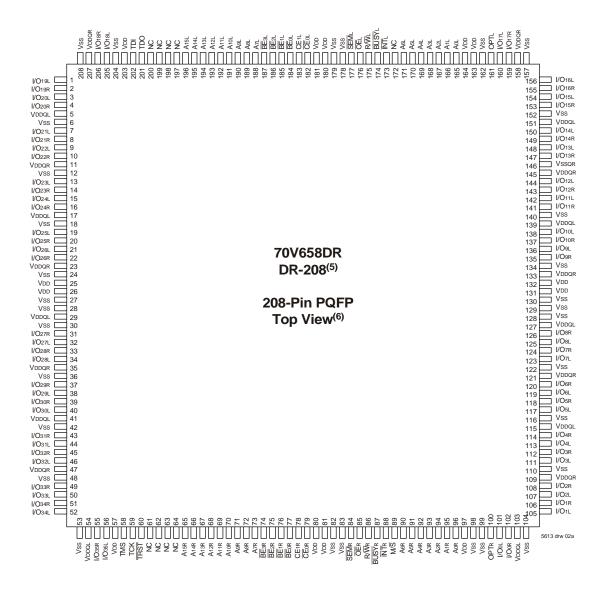
Pin Configurations(1,2,3,4)

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	
Α	I/O19L	I/O18L	Vss	TDO	NC	NC	A12L	A8L	BE ₁ L	VDD	SEML	ĪNTL	A4L	AoL	OPT∟	I/O17L	Vss	Α
В	I/O20R	Vss	I/O18R	TDI	NC	A13L	A9L	BE ₂ L	<u>CE</u> ₀L	Vss	BUSYL	A5L	A1L	Vss	VDDQR	I/O16L	I/O15R	В
С	VDDQL	I/O _{19R}	VDDQR	VDD	NC	A14L	A10L	BE _{3L}	CE ₁ L	Vss	R/WL	A6L	A ₂ L	VDD	I/O16R	I/O ₁₅ L	Vss	С
D	I/O22L	Vss	I/O21L	I/O20L	A15L	A11L	A7L	BE ₀ L	VDD	ŌĒL	NC	Азь	VDD	I/O17R	VDDQL	I/O14L	I/O14R	D
Е	I/O23L	I/O22R	VDDQR	I/O21R										I/O12L	I/O13R	Vss	I/O13L	Ε
F	VDDQL	I/O23R	I/O24L	Vss										Vss	I/O12R	I/O11L	VDDQR	F
G	I/O ₂₆ L	Vss	I/O25L	I/O24R										I/O ₉ L	VDDQL	I/O10L	I/O _{11R}	G
Н	VDD	I/O26R	VDDQR	I/O25R)V658 F-20					VDD	I/O9R	Vss	I/O10R	Н
J	VDDQL	VDD	Vss	Vss							٨			Vss	VDD	Vss	VDDQR	J
K	I/O _{28R}	Vss	I/O27R	Vss					Ball f p Vie		A			I/O7R	VDDQL	I/O8R	Vss	K
L	I/O29R	I/O _{28L}	VDDQR	I/O27L										I/O6R	I/O7L	Vss	I/O8L	L
М	VDDQL	I/O29L	I/O30R	Vss										Vss	I/O6L	I/O5R	VDDQR	М
N	I/O31L	Vss	I/O31R	I/O30L										I/O3R	VDDQL	I/O4R	I/O ₅ L	N
Р	I/O32R	I/O32L	VDDQR	I/O35R	TRST	NC	A12R	A8R	BE1R	VDD	SEMR	ĪNTr	A4R	I/O ₂ L	I/O3L	Vss	I/O4L	Р
R	Vss	I/O33L	I/O34R	тск	NC	A13R	A9R	BE _{2R}	<u>CE</u> ∂R	Vss	BUSYR	A ₅ R	A1R	Vss	VDDQL	I/O1R	VDDQR	R
Т	I/O33R	I/O ₃₄ L	VDDQL	TMS	NC	A14R	A10R	BE _{3R}	CE1R	Vss	R/W̄R	A6R	A ₂ R	Vss	I/Oor	Vss	I/O ₂ R	Т
U	Vss	I/O35L	VDD	NC	A15R	A11R	A7R	BEOR	VDD	ŌĒR	M/S	Дзя	Aor	VDD	OPTR	I/OoL	I/O1L	U

5613 tbl 02b

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIH (0V)
- 3. All Vss pins must be connected to ground.
- 4. Package body is approximately 15mm x 15mm x 1.4mm with 0.8mm ball pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configurations(1,2,3,4) (con't.)



- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V)
- 3. All Vss pins must be connected to ground.
- 4. Package body is approximately 28mm x 28mm x 3.5mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Configuration^(1,2,3,4) (con't.)

70V658BC BC-256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	TDI	NC	NC	A14L	A11L	A8L	BE ₂ L	CE1L	OEL	INTL	A 5L	A2L	A ₀ L	NC	NC
B1	B2	B3	B4	B5	B6	B7	BE3L	B9	B10	B11	B12	B13	B14	B15	B16
I/O18L	NC	TDO	NC	A15L	A12L	A9L		CE0L	R/WL	NC	A4L	A1L	NC	I/O17L	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
I/O18R	I/O _{19L}	Vss	NC	A13L	A10L	A7L	BE ₁ L	BE ₀ L	SEML	BUSYL	A ₆ L	A ₃ L	OPTL	I/O17R	I/O16L
D1	D2	D3	D4	d5	D6	d7	d8	d9	d10	D11	D12	D13	D14	D15	D16
I/O _{20R}	I/O19R	I/ O 20L	Vdd	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	I/O15R	I/O15L	I/O16R
E1	E2	E3	E4	E5	E6	E7	E8	E9	E10	E11	E12	E13	E14	E15	E16
I/O21R	I/O21L	I/O22L	Vddql	Vdd	V _{DD}	Vss	Vss	Vss	Vss	V _{DD}	VDD	Vddqr	I/O13L	I/O14L	I/O14R
F1	F2	F3	F4	F5	F6	F7	F8	F9	F10	F11	F12	F13	F14	F15	F16
I/O ₂₃ L	I/O _{22R}	I/O _{23R}	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O _{12R}	I/O13R	I/O12L
G1	G2	G3	g4	G5	G6	G7	G8	G9	G10	G11	G12	G13	G14	G15	G16
I/O24R	I/O _{24L}	I/O25L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O10L	I/O11L	I/O11R
H1	H2	H3	h4	H5	H6	H7	н8	н9	H10	H11	H12	H13	H14	H15	H16
I/O _{26L}	I/O _{25R}	I/O26R	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/ O 9R	IO 9L	I/O _{10R}
J1	J2	J3	J4	J5	J6	J7	_{J8}	^{J9}	J10	J11	J12	J13	J14	J15	J16
I/O27L	I/ O 28R	I/ O 27R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O8R	I/ O 7R	I/O8L
K1	K2	K3	k4	K5	K6	K7	K8	к9	K10	K11	K12	K13	K14	K15	K16
I/O29R	I/ O 29L	I/O28L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O6R	I/O6L	I/O7L
L1	L2	L3	l4	L5	L6	L7	L8	L9	L10	L11	L12	L13	L14	L15	L16
I/O ₃₀ L	I/O31R	I/O _{30R}	Vddqr	VDD	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O ₅ L	I/O4R	I/O _{5R}
M1	M2	M3	M4	M5	M6	M7	M8	м9	M10	M11	M12	M13	M14	M15	M16
I/O32R	I/O32L	I/O31L	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddql	I/O3R	I/O3L	I/O4L
N1	N2	N3	N4	N5	N6	n7	n8	n9	N10	N11	N12	N13	N14	N15	N16
I/O33L	I/O34R	I/O33R	Vdd	VDDQR	VDDQR	Vddql	Vddql	Vddqr	VDDQR	VDDQL	Vddql	VDD	I/ O 2L	I/O1R	I/O ₂ R
P1	P2	P3	P4	P5	P6	P7	P8	P9	P10	P11	P12	P13	P14	P15	P16
I/O35R	I/O34L	TMS	NC	A13R	A10R	A7R	BE1R	BE0R	SEMR	BUSYR	A6R	A3R	I/OoL	I/O0R	I/O1L
R1	R2	R3	R4	R5	R6	R7	R8	R9	R10	R11	R12	R13	R14	R15	R16
I/O ₃₅ L	NC	TRST	NC	A 15R	A12R	A 9R	BE3R	CE0R	R/W R	M/S	A4R	A1R	OPTR	NC	NC
T1	T2	T3	T4	T5	T6	T7	T8	T9	T10	T11	T12	T13	T14	T15	T16
NC	TCK	NC	NC	A 14R	A11R	A8R	BE2R	CE1R	OE R	INTR	A 5R	A2R	A 0R	NC	NC

5613 drw 02c

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

Pin Names

Left Port	Right Port	Names			
	•				
CEOL, CE1L	CEOR, CE1R	Chip Enables			
R/WL	R/W̄R	Read/Write Enable			
ŌĒL	OE R	Output Enable			
A0L - A15L	A0R - A15R	Address			
I/O0L - I/O35L	I/Oor - I/O35R	Data Input/Output			
SEML	SEMR	Semaphore Enable			
ĪNTL	ĪNTr	Interrupt Flag			
BUSYL	<u>BUS</u> YR	Busy Flag			
BEOL - BE3L	BEOR - BE3R	Byte Enables (9-bit bytes)			
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾			
OPTL	OPTr	Option for selecting VDDQX ^(1,2)			
M	ΙS̄	Master or Slave Select			
V	DD	Power (3.3V) ⁽¹⁾			
V	SS	Ground (0V)			
Т	DI	Test Data Input			
π	00	Test Data Output			
TO	CK	Test Logic Clock (10MHz)			
Π	MS	Test Mode Select			
ĪĪ	ST	Reset (Initialize TAP Controller)			

5613 tbl 01

- VDD, OPTx, and VDDOx must be set to appropriate operating levels prior to applying inputs on I/Ox.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDOX must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and controls will operate at 2.5V levels and VDDOX must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

Truth Table I—Read/Write and Enable Control^(1,2)

ŌĒ	SEM	<u>CE</u> ₀	CE1	BE ₃	BE₂	BE ₁	BE ₀	R/W	Byte 3 I/O27-35	Byte 2 I/O ₁₈₋₂₆	Byte 1 I/O ₉₋₁₇	Byte 0 I/O ₀₋₈	MODE
Х	Н	Н	Χ	Х	Χ	Χ	Χ	Χ	High-Z	High-Z	High-Z	High-Z	Deselected-Power Down
Х	Н	Χ	L	Χ	Χ	Χ	Χ	Χ	High-Z	High-Z	High-Z	High-Z	Deselected-Power Down
Х	Н	L	Н	Н	Н	Н	Н	Х	High-Z	High-Z	High-Z	High-Z	All Bytes Deselected
Х	Н	L	Н	Н	Н	Н	L	L	High-Z	High-Z	High-Z	Din	Write to Byte 0 Only
Х	Н	L	Н	Н	Н	L	Н	L	High-Z	High-Z	Din	High-Z	Write to Byte 1 Only
Х	Н	L	Н	Н	L	Н	Н	L	High-Z	Din	High-Z	High-Z	Write to Byte 2 Only
Х	Н	L	Н	L	Н	Н	Н	L	DIN	High-Z	High-Z	High-Z	Write to Byte 3 Only
Х	Н	L	Н	Н	Н	L	L	L	High-Z	High-Z	Din	Din	Write to Lower 2 Bytes Only
Х	Н	L	Н	L	L	Н	Н	L	Din	Din	High-Z	High-Z	Write to Upper 2 bytes Only
Х	Н	L	Н	L	L	L	L	L	Din	Din	Din	DIN	Write to All Bytes
L	Н	L	Н	Н	Н	Н	L	Н	High-Z	High-Z	High-Z	Dout	Read Byte 0 Only
L	Н	L	Н	Н	Н	L	Н	Н	High-Z	High-Z	Dоит	High-Z	Read Byte 1 Only
L	Н	L	Н	Н	L	Н	Н	Н	High-Z	Douт	High-Z	High-Z	Read Byte 2 Only
L	Н	L	Н	L	Н	Н	Н	Н	Dout	High-Z	High-Z	High-Z	Read Byte 3 Only
L	Н	L	Н	Н	Н	L	L	Н	High-Z	High-Z	Dоит	Dout	Read Lower 2 Bytes Only
L	Н	L	Н	L	L	Н	Н	Н	Douт	Douт	High-Z	High-Z	Read Upper 2 Bytes Only
L	Н	L	Н	L	L	L	L	Н	Douт	D оит	Dоит	Dout	Read All Bytes
Н	Н	L	Н	L	L	L	L	Χ	High-Z	High-Z	High-Z	High-Z	Outputs Disabled

NOTES: 5613 tbl 02

Truth Table II – Semaphore Read/Write Control(1)

			Inp	uts ⁽¹⁾				Out	puts	
ŒĒ ⁽²⁾	R/W	ŌĒ	BE ₃	BE ₂	<u>B</u> E₁	BE₀	SEM	I/O1-35	I/Oo	Mode
Н	Н	L	L	L	L	L	L	DATA out	DATAout	Read Data in Semaphore Flag ⁽³⁾
Н	1	Χ	Χ	Χ	Χ	L	L	Х	DATAIN	Write I/O₀ into Semaphore Flag
L	Χ	X	X	Х	Χ	Χ	L			Not Allowed

NOTES

- 1. There are eight semaphore flags written to I/Oo and read from all the I/Os (I/Oo-I/O35). These eight semaphore flags are addressed by Ao-A2.
- 2. $\overline{CE} = L$ occurs when $\overline{CE}_0 = V_{IL}$ and $CE_1 = V_{IH}$.
- 3. Each byte is controlled by the respective $\overline{BE}n$. To read data $\overline{BE}n$ = VIL.

^{1. &}quot;H" = VIH, "L" = VIL, "X" = Don't Care.

^{2.} It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	VDD			
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV			
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV			

NOTE:

1. This is the parameter Ta. This is the "instant on" case temperature.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
ЮПТ	DC Output Current	50	mA

NOTES:

5613 tbl 05

5613 tbl 04

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ VDD + 150mV.

Capacitance⁽¹⁾

(Ta = +25°C, F = 1.0MHz) PQFP ONLY

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	V _{IN} = 3dV	8	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	pF

NOTES:

- These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	٧
Vss	Ground	0	0	0	٧
VIH	Input High Voltage ⁽³⁾ (Address & Control Inputs)	1.7		VDDQ + 100mV ⁽²⁾	V
Vн	Input High Voltage - I/O ⁽³⁾	1.7	_	VDDQ + 100mV ⁽²⁾	٧
VIL	Input Low Voltage	-0.5 ⁽¹⁾		0.7	V

NOTES:

- 5613 tbl 06
- 1. $V_{IL \ge} -1.5V$ for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 100mV.
- To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (OV), and VDDOX for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDQ at 3.3V

Symbol	Parameter	Min.	Тур.	Мах.	Unit
VDD	Core Supply Voltage	3.15	3.3	3.45	٧
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	٧
Vss	Ground	0	0	0	٧
VIH	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0		VDDQ + 150mV ⁽²⁾	V
VIH	Input High Voltage - I/O ⁽³⁾	2.0	-	VDDQ + 150mV ⁽²⁾	V
VIL	Input Low Voltage	-0.3(1)	_	0.8	V

5613 tbl 07

NOTES:

- 1. $V_{IL \ge}$ -1.5V for pulse width less than 10 ns.
- 2. VTERM must not exceed VDDQ + 150mV.
- To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to ViH (3.3V), and VDDOX for that port must be supplied as indicated above.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 150mV)

			70V	658S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	$V_{DDQ} = Max., V_{IN} = 0V \text{ to } V_{DDQ}$	_	10	μA
ILO	Output Leakage Current	$\overline{CE}_0 = V_{IH} \text{ or CE}_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{DDQ}$	_	10	μΑ
Vol (3.3V)	Output Low Voltage ⁽²⁾	IOL = +4mA, $VDDQ = Min$.	_	0.4	V
Vон (3.3V)	Output High Voltage ⁽²⁾	IOH = -4mA, VDDQ = Min.	2.4		V
Vol (2.5V)	Output Low Voltage ⁽²⁾	IOL = +2mA, $VDDQ = Min$.	_	0.4	V
Vон (2.5V)	Output High Voltage ⁽²⁾	IOH = -2mA, VDDQ = Min.	2.0	_	V

NOTF:

5613 tbl 09

- 1. At $VDD \le -2.0V$ input leakages are undefined.
- 2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ (VDD = 3.3V ± 150mV)

		p.p		·											
										70V658S10 Com'l Only		58S12 m'l Ind	70V658S15 Com'l & Ind		
Symbol	Parameter	Test Condition	Version		Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit				
ldd	Dynamic Operating Current (Both	CEL and CER= VIL,	COM'L	S	340	500	315	465	300	440	mA				
	Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	S	_	_	365	515	350	490					
ISB1	Standby Current	CEL = CER = VIH	COM'L	S	115	165	90	125	75	100	mA				
	(Both Ports - TTL Level Inputs)	$f = f_{MAX}^{(1)}$	IND	S	_	_	115	150	100	125					
ISB2	Standby Current	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	225	340	200	325	175	315	mA				
	(One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S	_	_	225	365	200	350					
ISB3	Full Standby Current	Both Ports CEL and	COM'L	S	3	15	3	15	3	15	mA				
	(Both Ports - CMOS Level Inputs)	$\overline{CER} \ge VDD - 0.2V$, $VIN \ge VDD - 0.2V$ or $VIN \le 0.2V$, $f = 0^{(2)}$	IND	S	_	_	6	15	6	15					
ISB4	Full Standby Current	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VDD - 0.2V^{(5)}$	COM'L	S	220	335	195	320	170	310	mA				
	(One Port - CMOS Level Inputs)	$V_{IN} \ge V_{DD}$ - 0.2V or $V_{IN} \le 0.2V$, Active Port, Outputs Disabled, $f = f_{MAX}^{(1)}$	IND	S			220	360	195	345					

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, using "AC TEST CONDITIONS" at input levels of GND to 3V.
- 2. f = 0 means no address or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ).
- 5. $\overline{CE}x = VIL \text{ means } \overline{CE}0x = VIL \text{ and } CE1x = VIH$
 - $\overline{CE}x = VIH \text{ means } \overline{CE}0x = VIH \text{ or } CE1x = VIL$
 - $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{Vcc} 0.2 \text{V}$
 - $\overline{\text{CE}}\text{x} \ge \text{Vcc} 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \ge \text{Vcc} 0.2 \text{V}$ or CE1x 0.2 V
 - "X" represents "L" for left port or "R" for right port.

AC Test Conditions (VDDQ - 3.3V/2.5V)

Input Pulse Levels	GND to 3.0V / GND to 2.5V
Input Rise/Fall Times	2ns Max.
Input Timing Reference Levels	1.5V/1.25V
Output Reference Levels	1.5V/1.25V
Output Load	Figures 1 and 2

 833Ω DATAout-5pF* 770Ω

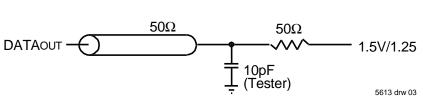


Figure 1. AC Output Test load.

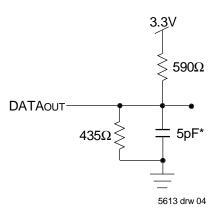


Figure 2. Output Test Load (For tcklz, tckHz, tolz, and toHz). *Including scope and jig.

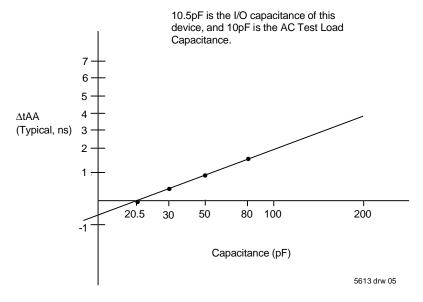


Figure 3. Typical Output Derating (Lumped Capacitive Load).

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁵⁾

		70V658S10 Com'l Only		70V658S12 Com'l & Ind		70V658S15 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	10		12	_	15	_	ns
taa	Address Access Time	_	10	_	12	_	15	ns
tace	Chip Enable Access Time ⁽³⁾	_	10	_	12	_	15	ns
tabe	Byte Enable Access Time ⁽³⁾	_	5	_	6	_	7	ns
taoe	Output Enable Access Time	_	5	_	6	_	7	ns
tон	Output Hold from Address Change	3	_	3	_	3	_	ns
t_z	Output Low-Z Time ^(1,2)	0	_	0	_	0	_	ns
tнz	Output High-Z Time ^(1,2)	0	4	0	6	0	8	ns
teu	Chip Enable to Power Up Time (2)	0	_	0	_	0	_	ns
tpp	Chip Disable to Power Down Time ⁽²⁾		10	_	10	_	15	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)		4	_	6		8	ns
tsaa	Semaphore Address Access Time	3	10	3	12	3	20	ns

5613 tbl 12

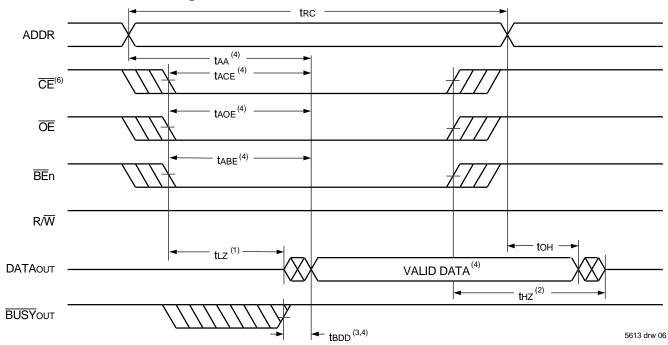
AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

			70V658S10 Com'l Only		70V658S12 Com'l & Ind		70V658S15 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE								
twc	Write Cycle Time	10	_	12	_	15	_	ns
tew	Chip Enable to End-of-Write ⁽³⁾	8	_	10	_	12	_	ns
taw	Address Valid to End-of-Write	8	_	10	_	12	_	ns
tas	Address Set-up Time ⁽³⁾	0	_	0	_	0	_	ns
twp	Write Pulse Width	8	_	10	_	12	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tow	Data Valid to End-of-Write	6	_	8	_	10	_	ns
tDH	Data Hold Time ⁽⁴⁾	0	_	0	_	0	_	ns
twz	Write Enable to Output in High-Z ^(1,2)	_	4	_	4	_	4	ns
tow	Output Active from End-of-Write ^(1,2,4)	0	_	0	_	0	_	ns
tswrd	SEM Flag Write to Read Time	5	_	5	_	5	_	ns
tsps	SEM Flag Contention Window	5	_	5	_	5	_	ns

NOTES:

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranted by device characterization, but is not production tested.
- 3. To access RAM, \overrightarrow{CE} = V_{IL} and \overrightarrow{SEM} = V_{IH}. To access semaphore, \overrightarrow{CE} = V_{IH} and \overline{SEM} = V_{IL}. Either condition must be valid for the entire tew time.
- 4. The specification for ton must be met by the device supplying write data to the RAM under all operating conditions. Although ton and tow values will vary over voltage and temperature, the actual ton will always be smaller than the actual tow.
- 5. These values are valid regardless of the power supply level selected for I/O and control signals (3.3V/2.5V). See page 5 for details.

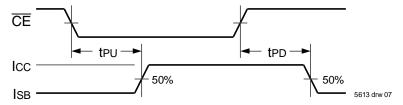
Waveform of Read Cycles⁽⁵⁾



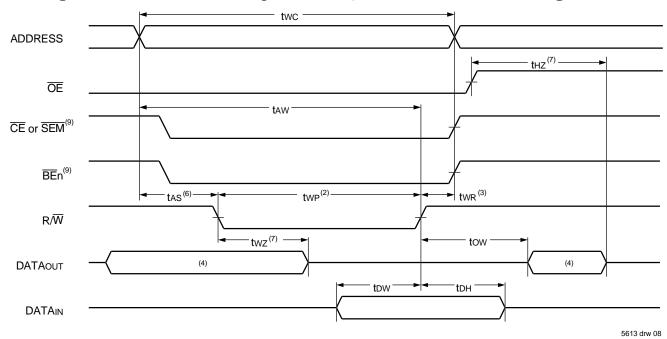
NOTES:

- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}},$ $\overline{\text{CE}}$ or $\overline{\text{BE}}\text{n}.$
- 2. Timing depends on which signal is de-asserted first \overline{CE} , \overline{OE} or $\overline{BE}n$.
- 3. tedd delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5. $\overline{SEM} = VIH.$

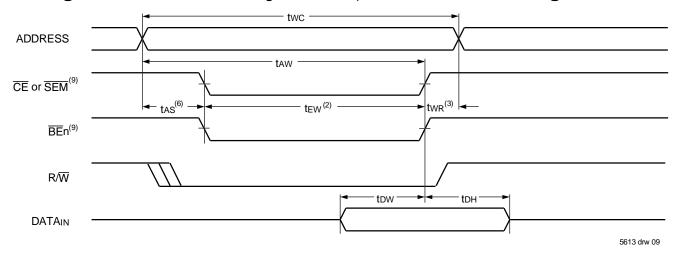
Timing of Power-Up Power-Down



Timing Waveform of Write Cycle No. 1, R/W Controlled Timing(1,5,8)

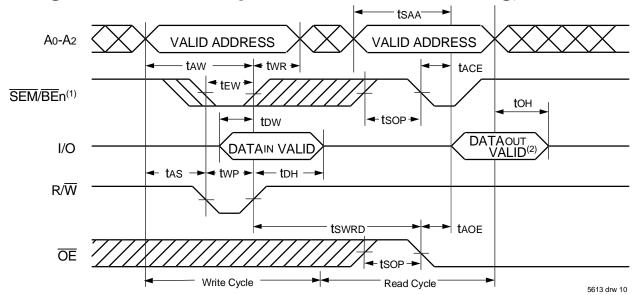


Timing Waveform of Write Cycle No. 2, $\overline{\text{CE}}$ Controlled Timing^(1,5)



- 1. $R\overline{W}$ or \overline{CE} or $\overline{BE}n = VIH$ during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a $\overline{CE} = V_{IL}$ and a $R/\overline{W} = V_{IL}$ for memory array writing cycle.
- 3. twn is measured from the earlier of $\overline{\text{CE}}$ or $\overline{\text{R/W}}$ (or $\overline{\text{SEM}}$ or $\overline{\text{R/W}}$) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the $\overline{\text{CE}}$ or $\overline{\text{SEM}} = \text{VIL}$ transition occurs simultaneously with or after the $\overline{\text{R/W}} = \text{VIL}$ transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, $\overline{\text{CE}}$ or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If $\overline{OE} = V_{IL}$ during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If $\overline{OE} = V_{IH}$ during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, $\overline{\text{CE}} = \text{V}_{\text{IL}}$ and $\overline{\text{SEM}} = \text{V}_{\text{IH}}$. To access semaphore, $\overline{\text{CE}} = \text{V}_{\text{IH}}$ and $\overline{\text{SEM}} = \text{V}_{\text{IL}}$. tew must be met for either condition.

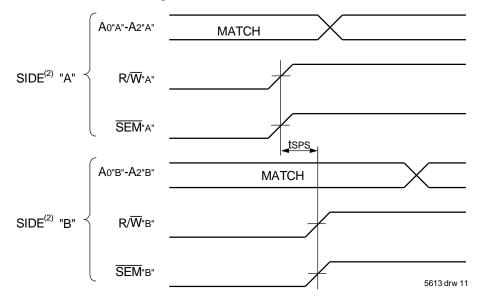
Timing Waveform of Semaphore Read after Write Timing, Either Side(1)



NOTES:

- 1. $\overline{\text{CE}} = \text{V}_{\text{IH}}$ for the duration of the above timing (both write and read cycle) (Refer to Chip Enable Truth Table). Refer also to Truth Table II for appropriate $\overline{\text{BE}}$ controls.
- 2. "DATAOUT VALID" represents all I/O's (I/Oo I/O35) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention(1,3,4)



- 1. Dor = Dol = VIL, $\overline{CE}L = \overline{CE}R = VIH$. Refer to Truth Table II for appropriate \overline{BE} control.
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. "B" is the opposite from port "A".
- 3. This parameter is measured from R/W*A* or SEM*A* going HIGH to R/W*B* or SEM*B* going HIGH.
- 4. If tsps is not satisfied, the semaphore will fall positively to one side or the other, but there is no guarantee which side will be granted the semaphore flag.

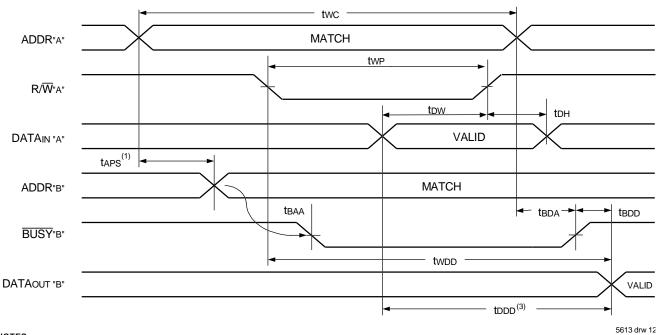
AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

C.mah al			70V658S10 Com'l Only		70V568S12 Com'l & Ind		70V658S15 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIMINO	G (M/S=VIH)							
tbaa	BUSY Access Time from Address Match	_	10		12	_	15	ns
t BDA	BUSY Disable Time from Address Not Matched	_	10		12	_	15	ns
t BAC	BUSY Access Time from Chip Enable Low		10		12		15	ns
tBDC	BUSY Disable Time from Chip Enable High		10		12		15	ns
taps	Arbitration Priority Set-up Time ⁽²⁾		_	5		5		ns
tBDD	BUSY Disable to Valid Data ⁽³⁾	_	10		12	_	15	ns
twн	Write Hold After BUSY ⁽⁵⁾	8	_	10		12	_	ns
BUSY TIMING	G (M/S=VIL)							
twB	BUSY Input to Write ⁽⁴⁾	0	_	0		0	_	ns
twн	Write Hold After BUSY ⁽⁵⁾		_	10	_	12	_	ns
PORT-TO-PO	rt delay timing							
twdd	Write Pulse to Data Delay ⁽¹⁾	_	22	_	25	_	30	ns
todd	Write Data Valid to Read Data Delay ⁽¹⁾		20		22	_	25	ns

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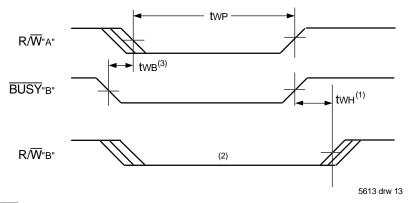
- 1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VIH)".
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of the Max. spec, twdd twp (actual), or tddd tdw (actual).
- 4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".
- 5. To ensure that a write cycle is completed on port "B" after contention on port "A".

Timing Waveform of Write with Port-to-Port Read and \overline{BUSY} (M/ \overline{S} = Vih)(2,4,5)



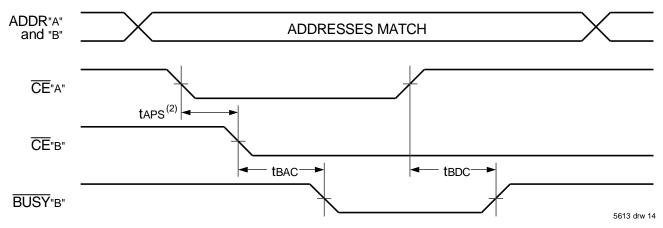
- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = VIL$ (SLAVE).
- 2. $\overline{CE}_L = \overline{CE}_R = V_{IL}$.
- 3. $\overline{OE} = V_{IL}$ for the reading port.
- 4. If $M/\overline{S} = VIL$ (slave), \overline{BUSY} is an input. Then for this example $\overline{BUSY}^*A^* = VIH$ and \overline{BUSY}^*B^* input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform of Write with \overline{BUSY} (M/ \overline{S} = VIL)

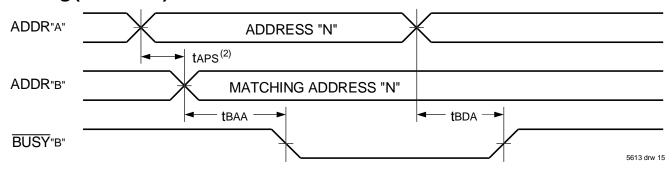


- 1. twn must be met for both \overline{BUSY} input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. two is only for the 'slave' version.

Waveform of \overline{BUSY} Arbitration Controlled by \overline{CE} Timing (M/ \overline{S} = ViH)⁽¹⁾



Waveform of \overline{BUSY} Arbitration Cycle Controlled by Address Match Timing (M/ \overline{S} = VIH)⁽¹⁾



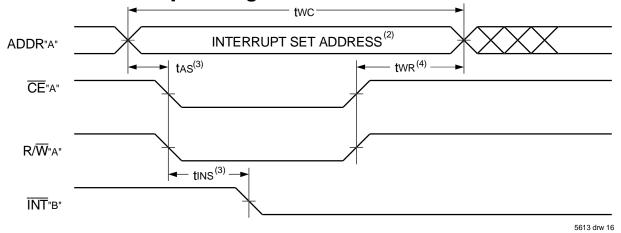
NOTES

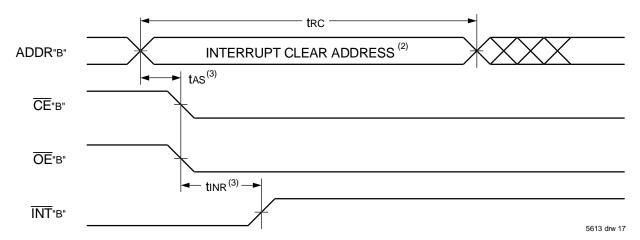
- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. If taps is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

			70V658S10 Com'l Only		70V658S12 Com'l & Ind		70V658S15 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRUPT TIMING								
tas	Address Set-up Time	0	-	0	_	0	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tins	Interrupt Set Time	_	10	_	12	_	15	ns
tinr	Interrupt Reset Time	_	10	_	12	_	15	ns

Waveform of Interrupt Timing(1)





NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. Refer to Interrupt Truth Table.
- Timing depends on which enable signal (CE or R/W) is asserted last.
 Timing depends on which enable signal (CE or R/W) is de-asserted first.

Truth Table III — Interrupt Flag^(1,4)

		Left Port Right Port								
R/WL	ĒĒ∟	ŌĒL	A15L-A0L	ΪΝΤι	R/W̄R	CER	OE R	A15R-A0R	Ī NT R	Function
L	L	Х	FFFF	Х	Х	Х	Х	X	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	FFFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	FFFE	Х	Set Left INTL Flag
Х	L	L	FFFE	H ⁽²⁾	Х	Х	Х	Χ	Х	Reset Left INTL Flag

NOTES:

- 1. Assumes $\overline{BUSY}_L = \overline{BUSY}_R = V_{IH}$.
- 2. If $\overline{BUSY}L = VIL$, then no change.
- 3. If $\overline{BUSY}R = VIL$, then no change.
- 4. INTL and INTR must be initialized at power-up.

Truth Table IV — Address BUSY Arbitration

Inputs			Out	puts	
ŒL	ՇĒ R	AOL-A15L AOR-A15R	BUSY _L (1)	BUSY _R (1)	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Χ	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

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NOTES:

- 1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70V658 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.
- 2. "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If taps is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

Truth Table V — Example of Semaphore Procurement Sequence (1,2,3)

Functions	Do - D35 Left	Do - D35 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES: 5613 bl 18

- 1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V658.
- 2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O35). These eight semaphores are addressed by Ao A2.
- 3. $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$ to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT70V658 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V658 has an automatic power down feature controlled by $\overline{\text{CE}}$. The $\overline{\text{CE}}$ 0 and CE1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected $(\overline{\text{CE}} = \text{HIGH})$. When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag $(\overline{\text{INT}}_L)$ is asserted when the right port writes to memory location

FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per the Truth Table. The left port clears the interrupt through access of address location FFFE when $\overline{CEL} = \overline{OEL} = VIL$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location FFFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location FFFF. The message (36 bits) at FFFE or FFFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations FFFE and FFFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

Busy Logic

IDT70V658S

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of BUSY logic is not desirable, the BUSY logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins HIGH. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port LOW.

The BUSY outputs on the IDT70V658 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

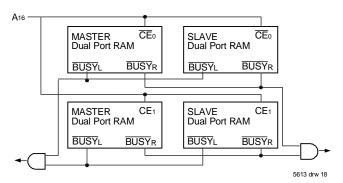


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V658 RAMs.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70V658 RAM array in width while using BUSY logic, one master part is used to decide which side of the RAMs array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the BUSY signal as a write inhibit signal. Thus on the IDT70V658 RAM the BUSY pin is an output if the part is used as a master (M/ \overline{S} pin = VIH), and the \overline{BUSY} pin is an input if the part used as a slave $(M/\overline{S} pin = VIL)$ as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration on a master is based on the chip enable and

address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with the R/W signal. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70V658 is an extremely fast Dual-Port 64K x 36 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, with both ports being completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from or written to at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by \overline{CE} , the Dual-Port RAM enable, and \overline{SEM} , the semaphore enable. The $\overline{\text{CE}}$ and $\overline{\text{SEM}}$ pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected.

Systems which can best use the IDT70V658 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V658s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V658 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that a shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then

verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinguished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT70V658 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the SEM pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{CE} R/ \overline{W} , and \overline{BE} n) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table V). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM, BEn) and output enable (OE) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or OE) to go inactive or the output will never change. However, during reads BEn functions only as an output for semaphore. It does not have any influence on the semaphore control logic.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will

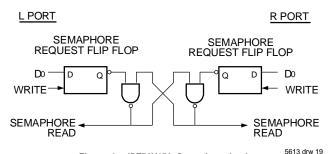


Figure 4. IDT70V658 Semaphore Logic

continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic quarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

JTAG Timing Specifications

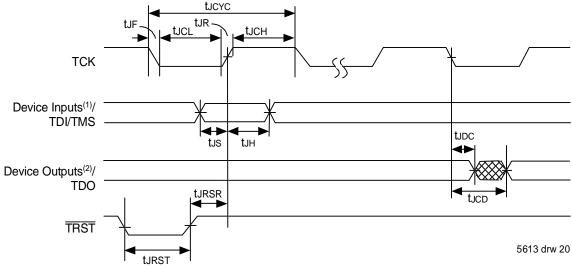


Figure 5. Standard JTAG Timing

NOTES:

- 1. Device inputs = All device inputs except TDI, TMS, and TRST.
- 2. Device outputs = All device outputs except TDO.

JTAG AC Electrical Characteristics^(1,2,3,4)

Symbol	Parameter	Min.	Max.	Units
tucyc	JTAG Clock Input Period	100	_	ns
tлсн	JTAG Clock HIGH	40	_	ns
tucL	JTAG Clock Low	40	_	ns
tur	JTAG Clock Rise Time	_	3 ⁽¹⁾	ns
₩	JTAG Clock Fall Time	_	3 ⁽¹⁾	ns
turst	JTAG Reset	50	_	ns
tursr	JTAG Reset Recovery	50	_	ns
tico	JTAG Data Output	_	25	ns
tido	JTAG Data Output Hold	0	_	ns
tus	JTAG Setup	15		ns
tлн	JTAG Hold	15	_	ns

NOTES:

- 1. Guaranteed by design.
- 30pF loading on external output signals. 3. Refer to AC Electrical Test Conditions stated earlier in this document.
- 4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

Identification Register Definitions

Instruction Field	Value	Description
Revision Number (31:28)	0x0	Reserved for version number
IDT Device ID (27:12)	0x30B	Defines IDT part number
IDT JEDEC ID (11:1)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	Indicates the presence of an ID register

5613 tbl 20

Scan Register Sizes

Register Name	Bit Size
Instruction (IR)	4
Bypass (BYR)	1
Identification (IDR)	32
Boundary Scan (BSR)	Note (3)

5613 tbl 21

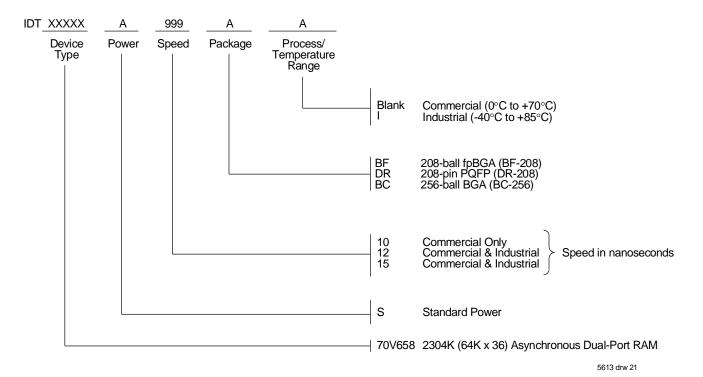
System Interface Parameters

Instruction	Code	Description
EXTEST	0000	Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.
BYPASS	1111	Places the bypass register (BYR) between TDI and TDO.
IDCODE	0010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.
HIGHZ	0100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers to a High-Z state.
CLAMP	0011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.
SAMPLE/PRELOAD	0001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ and outputs ⁽¹⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.
RESERVED	All other codes	Several combinations are reserved. Do not use codes other than those identified above.

NOTES

- 1. Device outputs = All device outputs except TDO.
- 2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}$.
- 3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

Ordering Information



Preliminary Datasheet: Definition

"PRELIMINARY' datasheets contain descriptions for products that are in early release.

Datasheet Document History:

6/2/00: Initial Public Offering.

Inserted additional BEn information on pages 6, 13, 20. 8/7/00:

6/20/01: Increased BUSY TIMING parameters tbda, tbac, tbdc, tbdc for all speeds on page 14.

Changed maximum value for JTAG AC Electrical Characteristics for tuco from 20ns to 25ns on page 21.



CORPORATE HEADQUARTERS

2975 Stender Way Santa Clara, CA 95054 for SALES:

800-345-7015 or 408-727-6116

fax: 408-492-8674 www.idt.com

for Tech Support: 831-754-4613

DualPortHelp@idt.com

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